



STB85NF55L STP85NF55L

N-channel 55 V, 0.0060 Ω , 80 A, TO-220, D²PAK
STripFET™ II Power MOSFET

Features

Type	V _{DSS}	R _{DS(on) max}	I _D
STB85NF55L	55 V	< 0.008 Ω	80 A
STP85NF55L	55 V	< 0.008 Ω	80 A

- Low threshold drive

Application

- Switching applications

Description

This Power MOSFET is the latest development of STMicroelectronics unique "single feature size" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

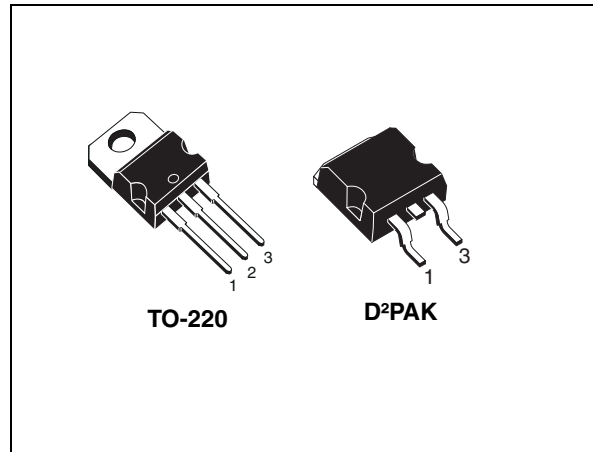


Figure 1. Internal schematic diagram

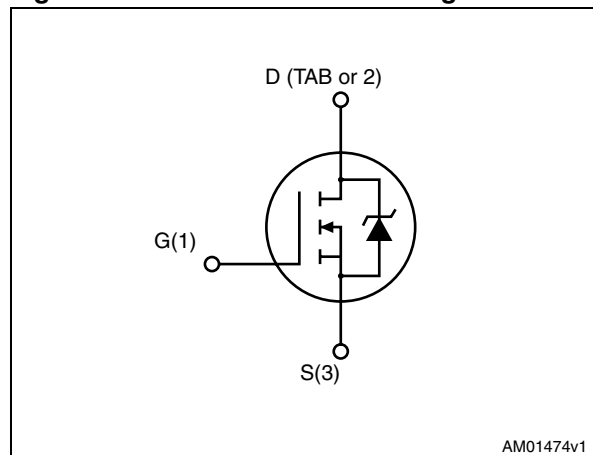


Table 1. Device summary

Order code	Marking	Package	Packaging
STB85NF55LT4	B85NF55L	D ² PAK	Tape and reel
STP85NF55L	P85NF55L	TO-220	Tube

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value		Unit
V _{DS}	Drain-source voltage (V _{GS} = 0)	55		V
V _{GS}	Gate-source voltage	± 15		V
I _D ⁽¹⁾	Drain current (continuous) at T _C = 25 °C	80		A
I _D ⁽¹⁾	Drain current (continuous) at T _C =100 °C	80		A
I _{DM} ⁽²⁾	Drain current (pulsed)	320		A
P _{TOT}	Total dissipation at T _C = 25 °C	300		W
	Derating factor	2.0		W/°C
dv/dt ⁽³⁾	Peak diode recovery voltage slope	10		V/ns
E _{AS} ⁽⁴⁾	Single pulse avalanche energy	980		mJ
T _J	Operating junction temperature	-55 to 175		°C
T _{stg}	Storage temperature			

1. Current limited by package
2. Pulse width limited by safe operating area
3. I_{SD} ≤ 80 A, di/dt ≤ 300 A/μs, V_{DD} ≤ V_{(BR)DSS}, T_J ≤ T_{JMAX}
4. Starting T_J = 25 °C, I_D = 40 A, V_{DD} = 40 V

Table 3. Thermal data

Symbol	Parameter	Value		Unit
		D ² PAK	TO-220	
R _{thj-case}	Thermal resistance junction-case max.	0.5		°C/W
R _{thj-amb}	Thermal resistance junction-ambient max.	62.5		°C/W
R _{thj-pcb}	Thermal resistance junction-pcb max. ⁽¹⁾	35		°C/W
T _l	Maximum lead temperature for soldering purpose	300		°C

1. When mounted on 1inch² FR-4 2Oz Cu board

2 Electrical characteristics

($T_{CASE} = 25\text{ °C}$ unless otherwise specified)

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 250\ \mu\text{A}$, $V_{GS} = 0$	55			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = \text{max rating}$, $V_{DS} = \text{max rating @ } 125\text{ °C}$			1 10	μA μA
I_{GSS}	Gate body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 15\text{ V}$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\ \mu\text{A}$	1	1.6	2.5	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{ V}$, $I_D = 40\text{ A}$		0.0060	0.008	Ω
		$V_{GS} = 5\text{ V}$, $I_D = 40\text{ A}$		0.008	0.01	

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$g_{fs}^{(1)}$	Forward transconductance	$V_{DS} = 15\text{ V}$, $I_D = 40\text{ A}$	-	130		S
C_{iss}	Input capacitance	$V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0$	-	4050		pF
C_{oss}	Output capacitance			860		pF
C_{rss}	Reverse transfer capacitance			300		pF
Q_g	Total gate charge	$V_{DD} = 27.5\text{ V}$, $I_D = 80\text{ A}$ $V_{GS} = 5\text{ V}$	-	80	110	nC
Q_{gs}	Gate-source charge			20		nC
Q_{gd}	Gate-drain charge			45		nC

1. Pulsed: pulse duration=300 μs , duty cycle 1.5%

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 27.5\text{ V}$, $I_D = 40\text{ A}$, $R_G = 4.7\ \Omega$, $V_{GS} = 5\text{ V}$ Figure 14 on page 8	-	35		ns
t_r	Rise time			165		ns
$t_{d(off)}$	Turn-off delay time			70	-	ns
t_f	Fall time			55		ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min	Typ.	Max	Unit
I_{SD}	Source-drain current		-		80	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		320	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 80 \text{ A}$, $V_{GS} = 0$	-		1.5	V
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD} = 80 \text{ A}$, $di/dt = 100 \text{ A}/\mu\text{s}$, $V_{DD} = 20 \text{ V}$, $T_J = 150 \text{ }^\circ\text{C}$ Figure 16 on page 8	-	80 240 6		ns nC A

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration=300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

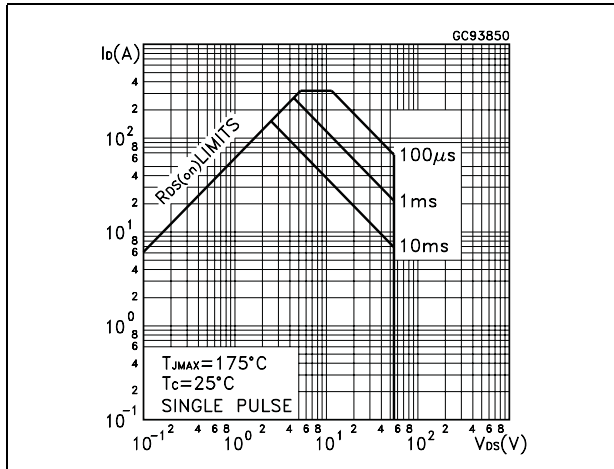


Figure 3. Thermal impedance

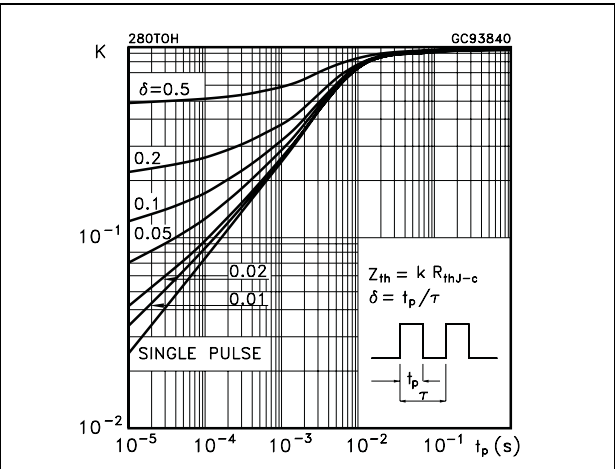


Figure 4. Output characteristics

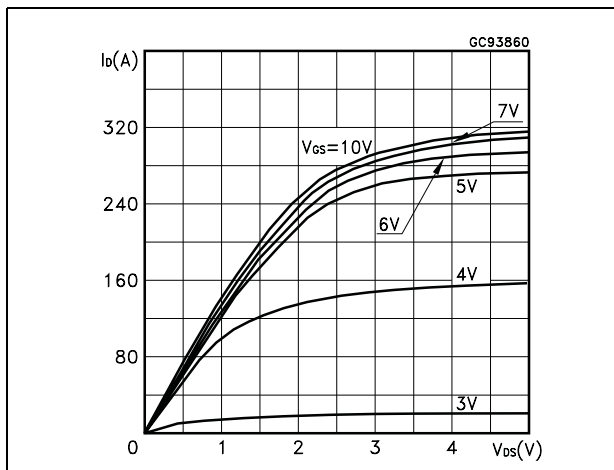


Figure 5. Transfer characteristics

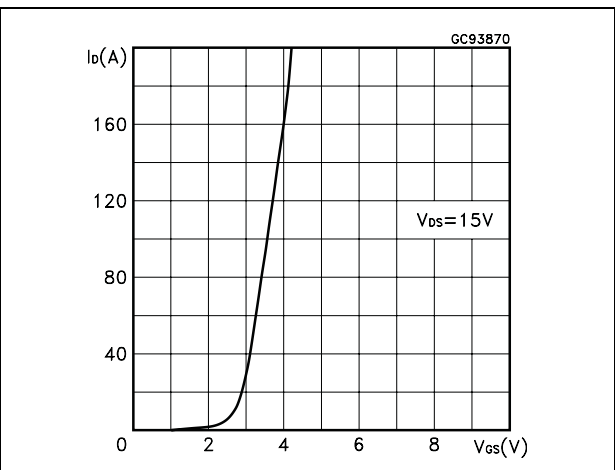


Figure 6. Transconductance

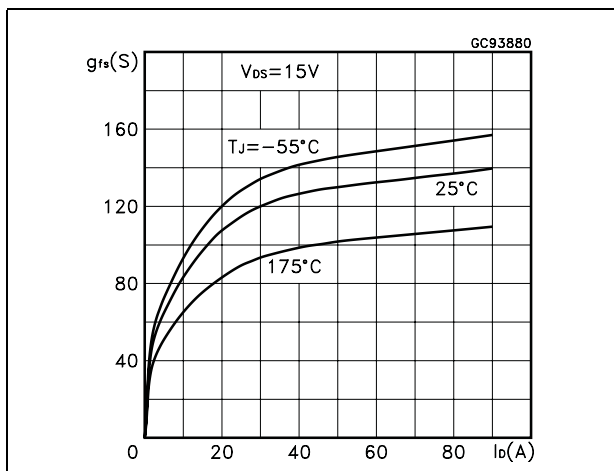


Figure 7. Static drain-source on resistance

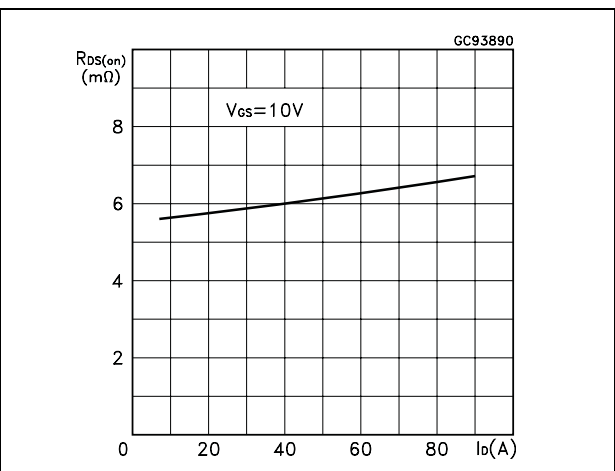


Figure 8. Gate charge vs gate-source voltage Figure 9. Capacitance variations

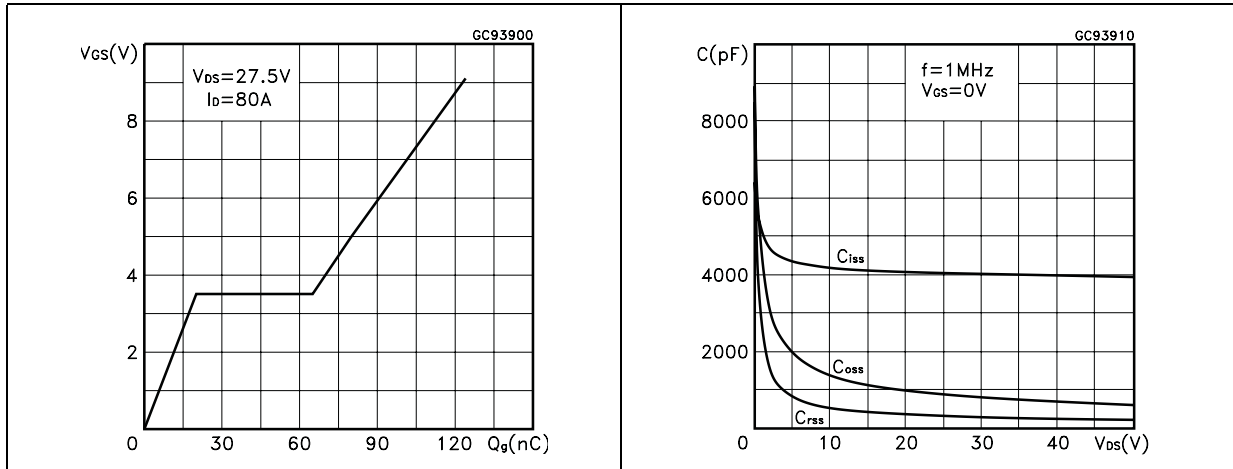


Figure 10. Normalized gate threshold voltage vs temperature Figure 11. Normalized on resistance vs temperature

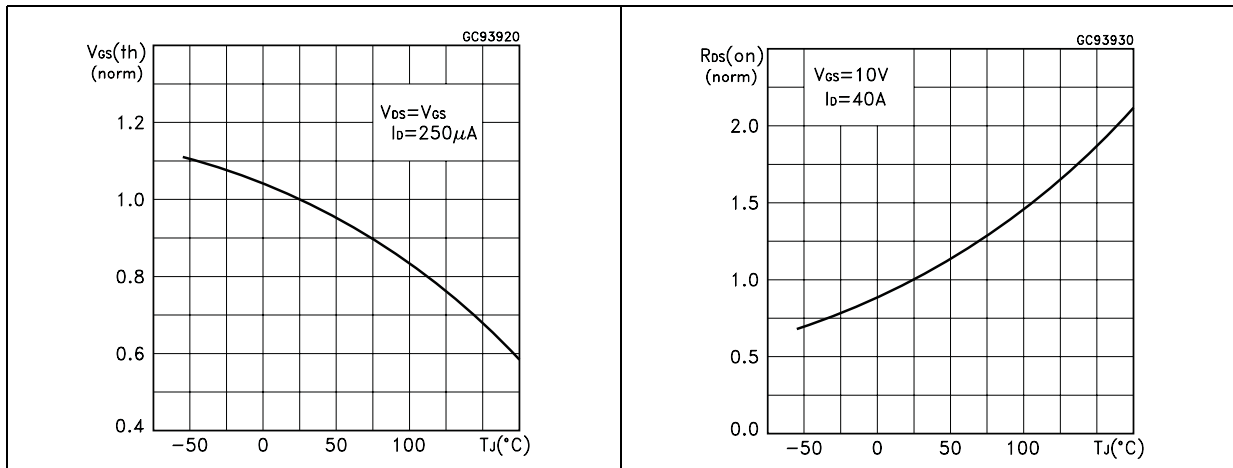
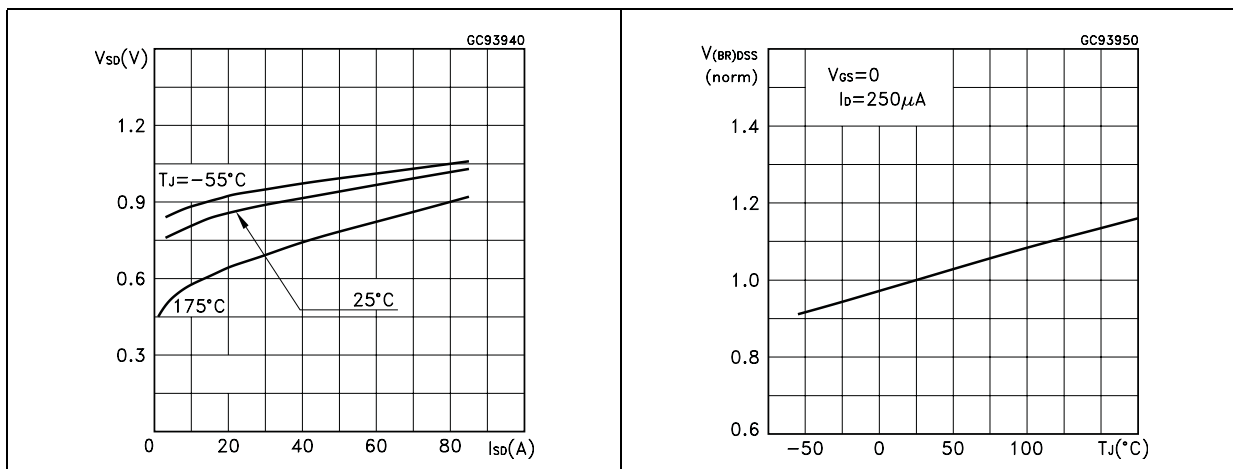


Figure 12. Source-drain diode forward characteristics Figure 13. Normalized B_{VDSS} vs temperature



3 Test circuits

Figure 14. Switching times test circuit for resistive load



Figure 15. Gate charge test circuit

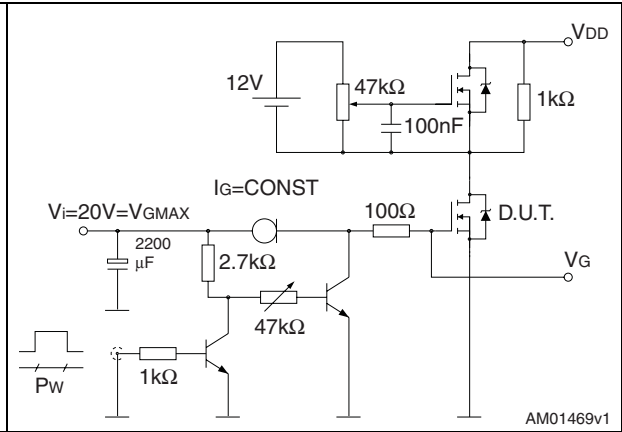


Figure 16. Test circuit for inductive load switching and diode recovery times

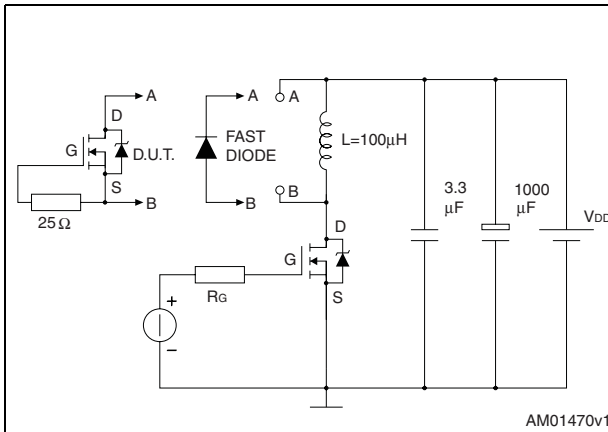


Figure 17. Unclamped inductive load test circuit

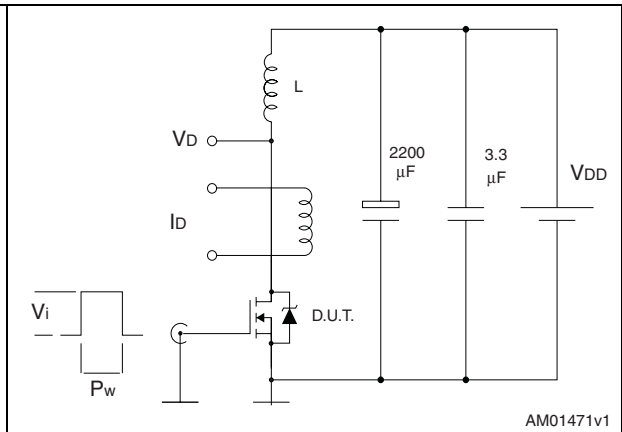
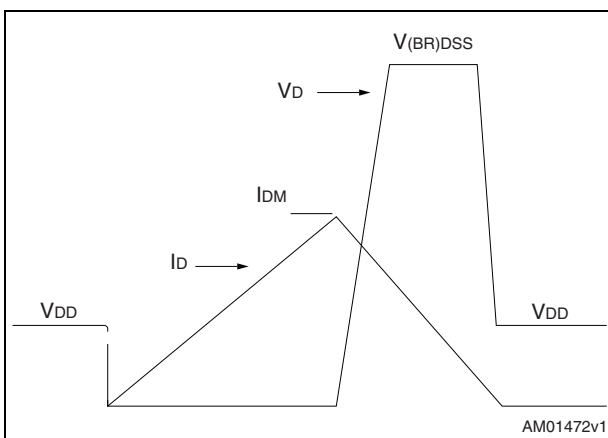


Figure 18. Unclamped inductive waveform

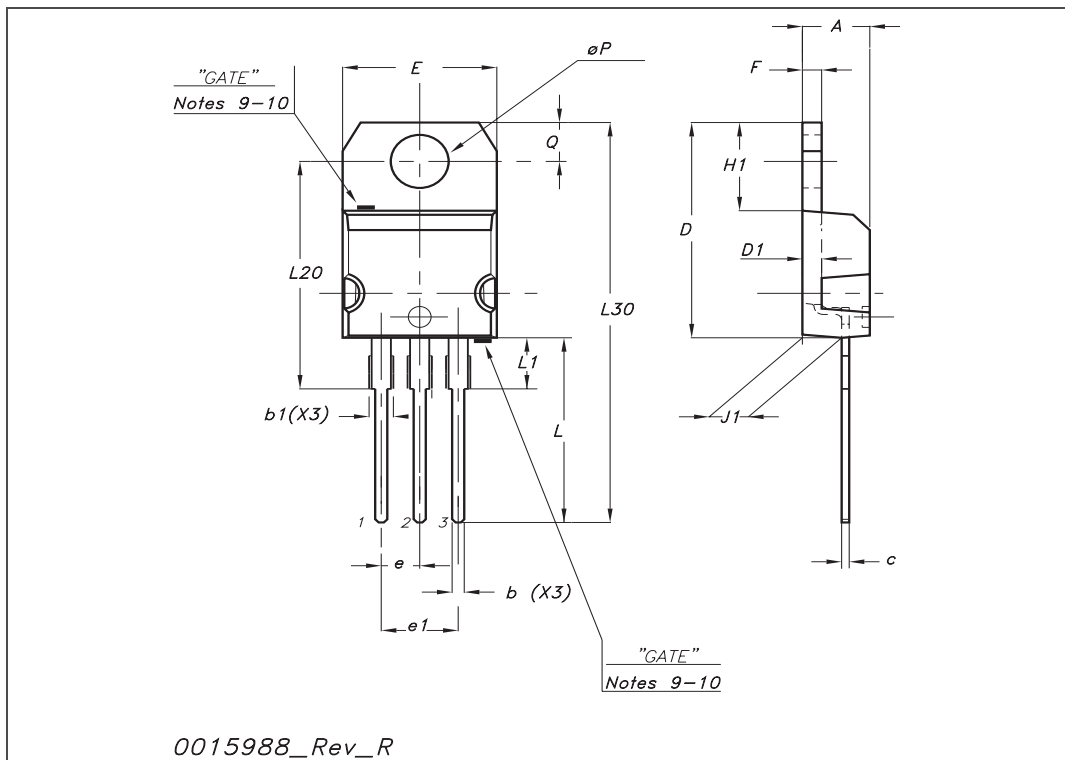


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

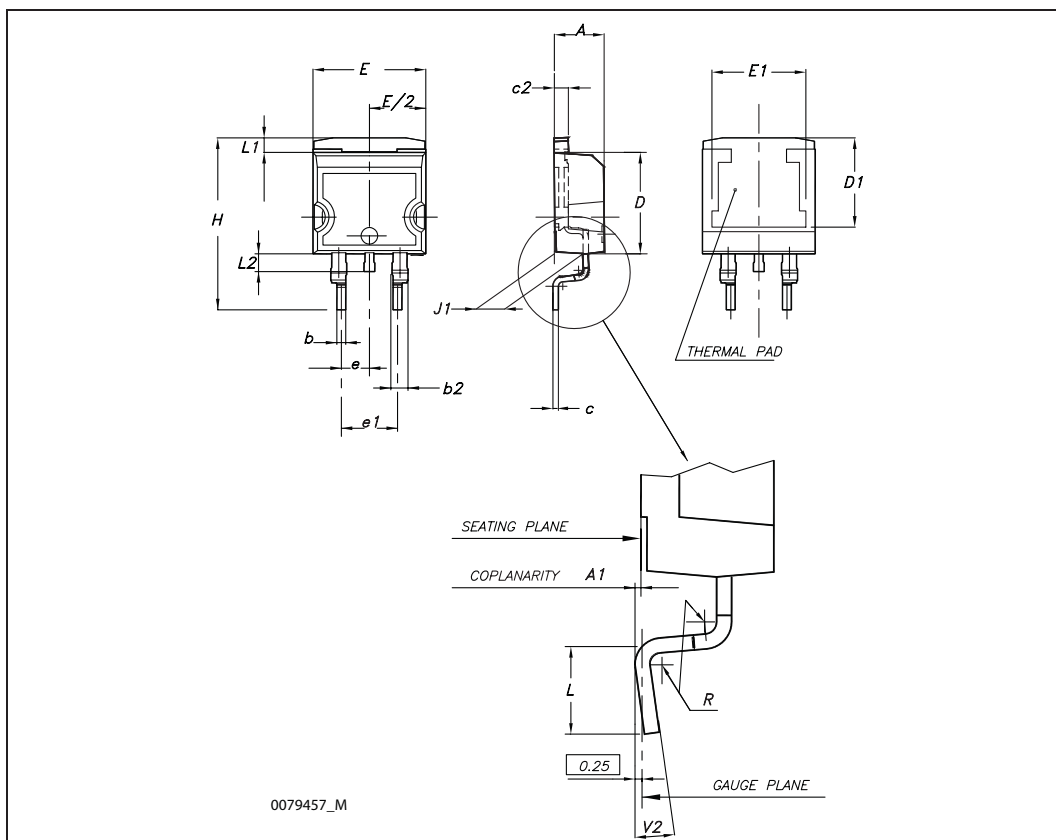
TO-220 mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.48		0.70	0.019		0.027
D	15.25		15.75	0.6		0.62
D1		1.27			0.050	
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.051
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
∅P	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



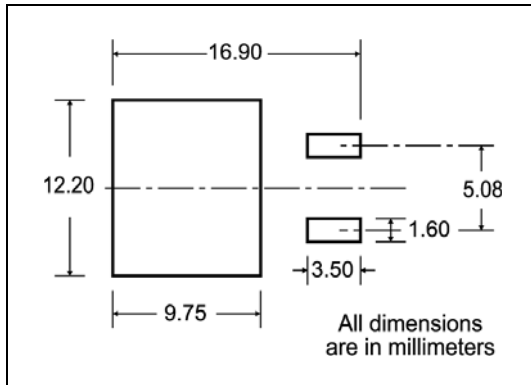
D²PAK (TO-263) mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
A1	0.03		0.23	0.001		0.009
b	0.70		0.93	0.027		0.037
b2	1.14		1.70	0.045		0.067
c	0.45		0.60	0.017		0.024
c2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1	7.50			0.295		
E	10		10.40	0.394		0.409
E1	8.50			0.334		
e		2.54			0.1	
e1	4.88		5.28	0.192		0.208
H	15		15.85	0.590		0.624
J1	2.49		2.69	0.099		0.106
L	2.29		2.79	0.090		0.110
L1	1.27		1.40	0.05		0.055
L2	1.30		1.75	0.051		0.069
R		0.4			0.016	
V2	0°		8°	0°		8°



5 Packaging mechanical data

D²PAK FOOTPRINT



TAPE AND REEL SHIPMENT

TAPE MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	10.5	10.7	0.413	0.421
B0	15.7	15.9	0.618	0.626
D	1.5	1.6	0.059	0.063
D1	1.59	1.61	0.062	0.063
E	1.65	1.85	0.065	0.073
F	11.4	11.6	0.449	0.456
K0	4.8	5.0	0.189	0.197
P0	3.9	4.1	0.153	0.161
P1	11.9	12.1	0.468	0.476
P2	1.9	2.1	0.075	0.082
R	50		1.574	
T	0.25	0.35	0.0098	0.0137
W	23.7	24.3	0.933	0.956

REEL MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0.795	
G	24.4	26.4	0.960	1.039
N	100		3.937	
T		30.4		1.197

BASE QTY	BULK QTY
1000	1000

6 Revision history

Table 8. Document revision history

Date	Revision	Changes
19-May-2009	7	New ECOPACK [®] statement in <i>Section 4: Package mechanical data</i> Content reworked to improve readability, no technical changes
06-Aug-2009	8	<i>Table 3: Thermal data</i> has been updated

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